

09/743982

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Application Information

Title Line One::	SILICON SINGLE CRYSTAL AND WAFER
Title Line Two::	DOPED WITH GALLIUM AND METHOD FOR

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Title Line Three:: PRODUCING THEM
Title Line Four::
Total Drawing Sheets:: 6
Docket Number:: 108360

Continuity Information

>This application is a:: 371
Application One:: PCT/JP00/02850
Filing Date:: April 28, 2000

Prior Foreign Applications

Foreign Application One:: 11-150697
Filing Date:: May 28, 1999
Country:: Japan
Priority Claimed:: Yes
Foreign Application Two:: 11-264549
Filing Date:: September 17, 1999
Country:: Japan
Priority Claimed:: Yes